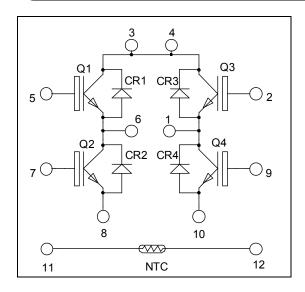
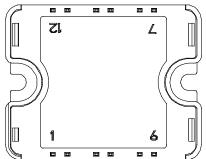


Full bridge High speed Trench + Field Stop IGBT4 Power Module

$$V_{CES} = 650V$$

 $I_{C} = 50A$ @ $Tc = 60$ °C





Pins 3/4 must be shorted together

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- High speed Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
- Very low stray inductance
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

All ratings @ $T_j = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings (per IGBT)

IIDDUIG	e maximum rucings (per 1051)			
Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Voltage		650	V
Ţ	Continuous Collector Current	$T_C = 25^{\circ}C$	70	
I_{C}	Continuous Collector Current $ T_{C} = 60^{\circ}C $	$T_C = 60$ °C	50	Α
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	140	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Power Dissipation		175	W

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.



Electrical	Characteristics	(per IGBT)
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Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 650V$				50	μΑ
V _{CE(sat)}	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$	1.4	1.85	2.3	V
	Conector Emitter Saturation Voltage	$I_C = 50A$	$T_j = 150$ °C		2.2		·
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 0.8 \text{ mA}$		4.2	5.1	5.6	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V$, $V_{CE} = 0V$				150	nA

Dynamic Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions	S	Min	Тур	Max	Unit
C _{ies}	Input Capacitance	$V_{GE} = 0V$			3100		
C _{oes}	Output Capacitance	$V_{CE} = 25V$			116		рF
C _{res}	Reverse Transfer Capacitance	f = 1MHz			90		
Q_{G}	Gate charge	$V_{GE} = 15V, I_{C} = V_{CE} = 480V$	$V_{GE} = 15V, I_C = 50A$ $V_{CE} = 480V$		315		nC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)			19		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 400V$			33		ns
$T_{d(off)}$	Turn-off Delay Time	$I_C = 50A$			197		
$T_{\mathbf{f}}$	Fall Time	$R_G = 7\Omega$			21		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C)			19		ns
T_{r}	Rise Time		$V_{GE} = \pm 15V$ $V_{Bus} = 400V$		29		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 400 V$ $I_{C} = 50 A$			227		
T_{f}	Fall Time	$R_G = 7\Omega$			22		
Eon	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 400V$	$T_j = 150$ °C		1.2		mJ
E _{off}	Turn off Energy	$I_C = 50A$ $R_G = 7\Omega$	$T_j = 150$ °C		1		1113
I_{sc}	Short Circuit data	$V_{GE} \le 15V ; V_{Bu}$ $t_p \le 5\mu s ; T_j = 15$			350		A
R_{thJC}	Junction to Case Thermal Resistance		_			0.85	°C/W

Diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V_{RRM}	Peak Repetitive Reverse Voltage					650	V
I_{RM}	Reverse Leakage Current	$V_R = 650V$				50	μΑ
I_F	DC Forward Current		$Tc = 25^{\circ}C$		50		A
V_{F}	Diode Forward Voltage	$I_F = 50A$	$T_i = 25^{\circ}C$		1.6	2	V
VF	Diode Polward Voltage	$V_{GE} = 0V$	$T_i = 150$ °C		1.5		v
t _{rr}	Reverse Recovery Time		$T_j = 25$ °C		100		ns
ι _{rr}	Reverse Recovery Time		$T_{j} = 150^{\circ}C$		150		113
0	Payarsa Racovary Charga	$I_F = 50A$ $V_R = 300V$	$T_j = 25$ °C		2.6		μС
Qrr	Q_{rr} Reverse Recovery Charge $V_R = 300V$ di/dt = $1800A/\mu s$	$T_{j} = 150^{\circ}C$		5.4		μС	
E_{rr}	Reverse Recovery Energy		$T_j = 25$ °C		0.6		mJ
Ŀrr	Reverse Recovery Energy		$T_{\rm j} = 150^{\circ}{\rm C}$		1.2		1113
R_{thJC}	Junction to Case Thermal Resistance					1.42	°C/W



Temperature sensor NTC (see application note APT0406 on www.microsemi.com).

Symbol	Characteristic		Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta \mathrm{B/B}$		$T_C=100$ °C		4		%

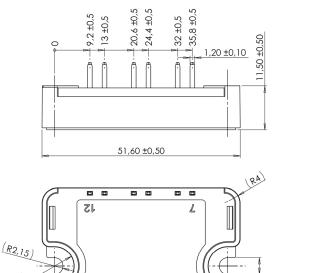
$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$

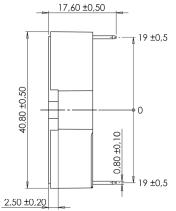
$$R_T: \text{ Thermistor value at T}$$

Thermal and package characteristics

Symbol	Characteristic	Min	Max	Unit		
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz					V
T_{J}	Operating junction temperature range			-40	175	
T_{JOP}	Recommended junction temperature under sv	Recommended junction temperature under switching conditions			T _J max -25	°C
T_{STG}	Storage Temperature Range			-40	125	
$T_{\rm C}$	Operating Case Temperature				125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				80	g

Package outline (dimensions in mm)





See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

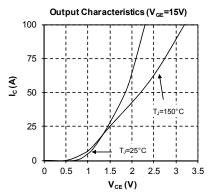
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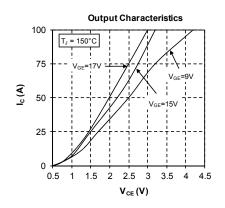
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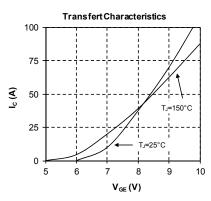
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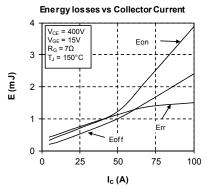


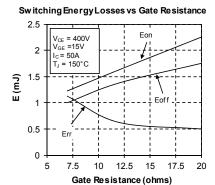
Typical performance curve

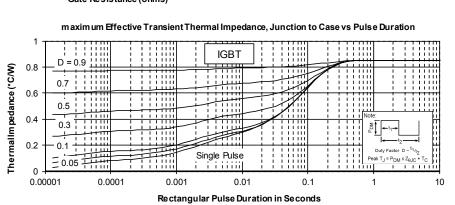






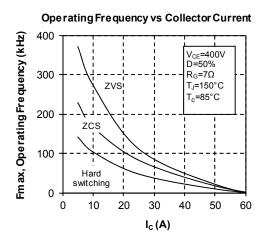


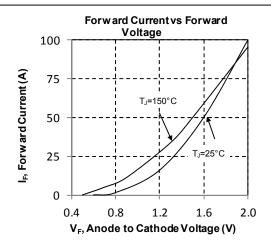




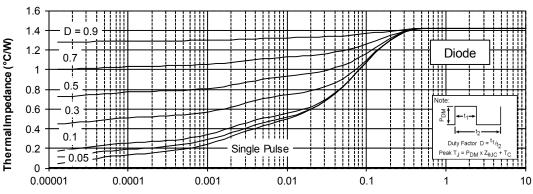
4 - 6







maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



Rectangular Pulse Duration in Seconds



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